

PATENT ABSTRACTS OF JAPAN

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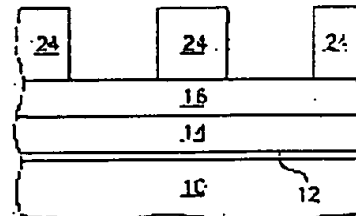
(54) SEMICONDUCTOR TREATMENT METHOD

(57)Abstract:

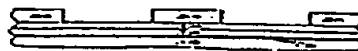
PROBLEM TO BE SOLVED: To provide an optical assist layer for optimizing a profile of resist patterns.

SOLUTION: A pad oxide 12 and a nitride layer 14 are formed on a substrate, and an optical assist layer 16 is formed before deposition of resist.

Thereafter, a resist layer is deposited to form resist patterns 24. These resist patterns 24 have a straight sidewall due to presence of the



optical assist layer 16 and does not form a resist 'foot' under the resist patterns 24. A



thickness of the optical assists layer 16 is optimized so as to reduce/remove interference between the resist layer and a substrate 10, and accordingly the resist 'foot' is reduced/removed.

LEGAL STATUS

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